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To cite this article: E Gorohova *et al* 2020 *J. Phys.: Conf. Ser.* **1695** 012041

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# Structure and spectral-luminescent properties of Er<sup>3+</sup>:ZnO optical ceramics

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**Abstract.** Transparent zinc oxide ceramics, undoped and doped with 0.1-2.0 wt% Er<sup>3+</sup> ions were fabricated by uniaxial hot pressing of commercial oxide powders. The ceramics were characterized by X-ray diffraction, SEM, EDX, Raman, X-ray and optical spectroscopy. The analysis of morphology of Er<sup>3+</sup>:ZnO ceramics reveals that the main components of texture are hexagonal prism planes similar to those for undoped ceramic. The ZnO grain size decreases with addition of Er<sub>2</sub>O<sub>3</sub>. The Er<sup>3+</sup> ions are distributed between the ZnO grains and the Er<sub>2</sub>O<sub>3</sub> crystals and do not enter the zinc oxide structure. The luminescence spectra of Er<sup>3+</sup>:ZnO ceramics contain emission bands originating from the intra-4f shell transitions of Er<sup>3+</sup> ions and bands assigned to defect states at ZnO. The X-ray luminescence spectra indicate the possible energy-transfer between the ZnO grains and Er<sup>3+</sup> ions. The defect luminescence band becomes weaker and the X-ray luminescence decay time decreases as the erbium concentration is increased.

## 1. Introduction

Zinc oxide is widely studied and applied in industry due to its unique properties of wide band gap of 3.37 eV, large exciton binding energy of 60 meV, excellent mechanical–electrical coupling characteristics, high radiation tolerance and low cost [1]. The ZnO performance can be adjusted by means of doping with rare-earth ions. In particular, an addition of Er<sup>3+</sup> ions may induce a variation of the luminescence properties of ZnO [2] while the 1.54 μm photoemission caused by Er<sup>3+</sup> intra-4f shell transition can be enhanced due to the ZnO → Er<sup>3+</sup> energy transfer [3]. In this work, both undoped and Er<sup>3+</sup>-doped ZnO optical ceramics were prepared. The effect of Er<sup>3+</sup> concentration on the microstructure, absorption and emission properties of ZnO ceramics were studied.

## 2. Experimental

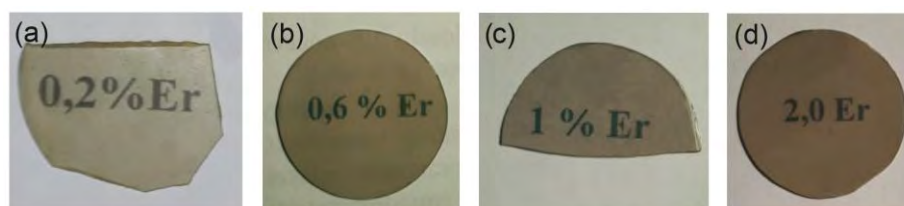
The undoped and Er<sup>3+</sup>-doped ZnO optical ceramics with the Er<sup>3+</sup> concentration of 0.1-2.0 wt% were fabricated from commercial reagent-grade ZnO and Er<sub>2</sub>O<sub>3</sub> powders by uniaxial hot pressing in vacuum at the temperatures of 1150 °C and 1180 °C. The as-sintered ceramic disks were polished to laser-



grade quality from both sides and finally had a diameter of 25 mm and a thickness of  $\sim 0.5$  mm. The undoped ceramic was pale green coloured. With  $\text{Er}^{3+}$  doping, the colour changed to rose-grey, Figure 1.

The X-ray powder diffraction (XRD) patterns of ceramics were measured with a Shimadzu XRD-6000 diffractometer, Ni-filtered  $\text{Cu K}\alpha$  radiation. The ZnO lattice parameters were determined by Rietveld refinement. The morphology of the polished surface of ceramics was characterized by scanning electron microscopy (SEM) using a MERLIN microscope (Carl Zeiss). The same microscope equipped with an Inca Energy X-Max analyzer was employed for energy dispersive X-ray (EDX) based element mapping. The grain size distribution was analyzed with the ImageJ software.

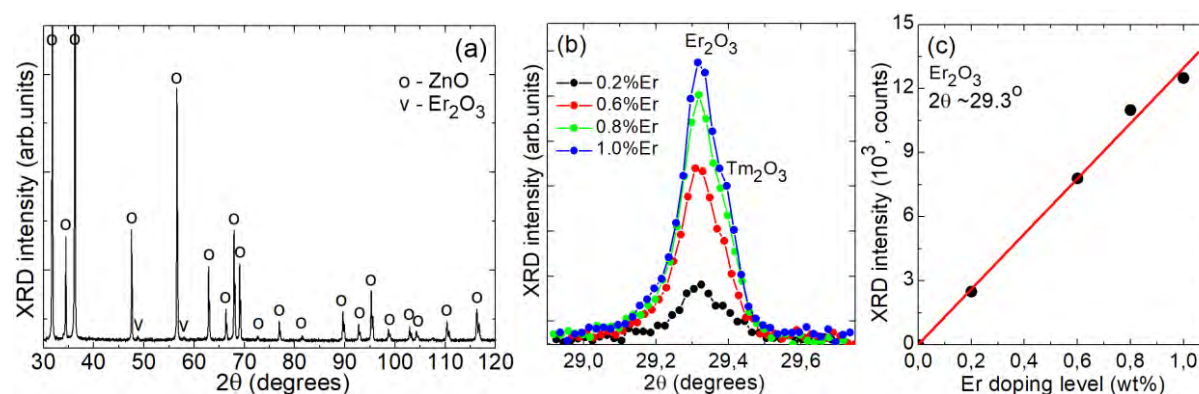
The Raman spectra were measured with the Renishaw inVia confocal Raman microscope using a Leica  $\times 50$  objective (N.A. = 0.75). The excitation wavelength  $\lambda_{exc}$  was 514 nm (an  $\text{Ar}^+$  ion laser). The total transmission spectra in the visible and near-IR were measured using a SPECORD 200 PLUS spectrophotometer. The absorption spectra in the range of 300 – 3300 nm were measured with a Shimadzu UV-3600 spectrophotometer. The spectra of photo-luminescence in the visible were recorded using the same confocal Raman microscope with  $\lambda_{exc} = 488$  nm. The luminescence at  $\sim 1.5 \mu\text{m}$  was measured using an optical spectrum analyser (AQ6375B, Yokogawa) under excitation by a Ti:Sapphire laser tuned to  $\lambda_{exc} = 800$  nm. The X-ray luminescence spectra were recorded in the reflection geometry upon continuous excitation by an X-ray tube with a tungsten anode (40 kV, 10 mA). The decay kinetics of X-ray luminescence was recorded using a pulsed X-ray setup with a pulse duration of  $\sim 1$  ns at a voltage of 30 kV and a current amplitude of 500 mA.



**Figure 1(a-d).** Photographs of  $\text{Er}^{3+}$ -doped ZnO transparent ceramics with different Er doping levels: (a) 0.2 wt%, (b) 0.6 wt%, (c) 1.0 wt% and (d) 2.0 wt%.

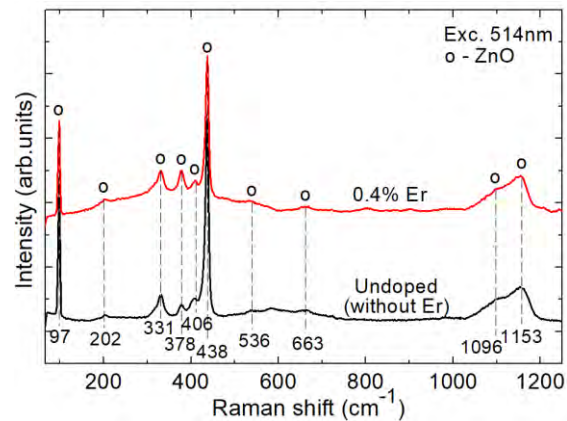
### 3. Results and discussion

A typical XRD pattern of  $\text{Er}^{3+}$ -doped ZnO ceramic displaying characteristic wurtzite-type peaks is shown in Figure 2(a). The calculated unit cell parameters for the  $\text{Er}^{3+}$ -doped ceramics nearly coincide

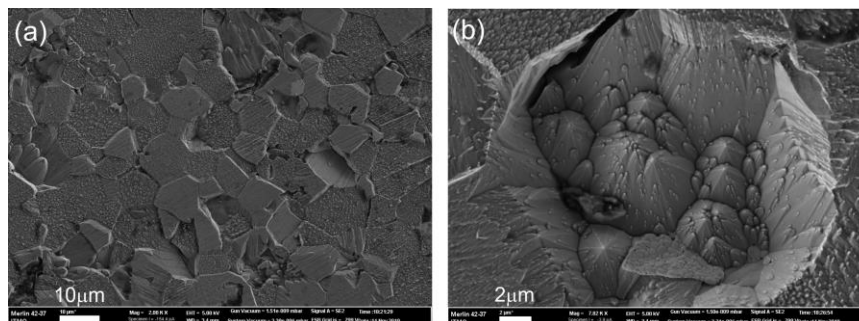


**Figure 2(a-c).** (a) XRD pattern of 1%  $\text{Er}^{3+}$  doped ZnO ceramic; (b) XRD patterns of ZnO:Er ceramic with different Er doping level in the  $2\theta$  range of 28.9 - 29.8° corresponding to the (222) peak of  $\text{Er}_2\text{O}_3$ ; (c) dependence of the diffraction peak intensity at  $2\theta \sim 29.3^\circ$  on the  $\text{Er}^{3+}$  concentration. The synthesis temperature is 1150 °C.

with the values obtained for the undoped ZnO ( $a = 3.249 \text{ \AA}$ ,  $c = 5.205 \text{ \AA}$ , ISDD card No 5-0664). It implies that  $\text{Er}^{3+}$  ions do not enter the ZnO structure. The presence of erbium ions in the form of pure  $\text{Er}_2\text{O}_3$  in ceramics is evidenced by weak diffraction peaks in the XRD pattern, Figure 2(a), located at diffraction angles  $2\theta = 49.4^\circ$  and  $58.6^\circ$  and corresponding to the Miller's indices  $(hkl) = (440)$  and  $(622)$ , respectively. The evidence of  $\text{Er}_2\text{O}_3$  crystallization is manifested by Figure 2(b). The presented fragment of the diffraction pattern for the angles  $2\theta$  of  $28.9\text{--}29.8^\circ$  contains an unambiguously assigned intense diffraction peak of  $\text{Er}_2\text{O}_3$  with  $(hkl) = (222)$  and much weaker side peak due to the possible traces of impurity  $\text{Tm}_2\text{O}_3$ . The diffraction intensity gradually increases with the  $\text{Er}^{3+}$  doping concentration, Figure 2(c).



**Figure 3.** Raman spectra of transparent ceramics: undoped ZnO and 0.4%  $\text{Er}^{3+}$ -doped ZnO,  $\lambda_{\text{exc}} = 514 \text{ nm}$ . Numbers indicate the Raman peak frequencies in  $\text{cm}^{-1}$ . The curves are shifted for the convenience of observation.

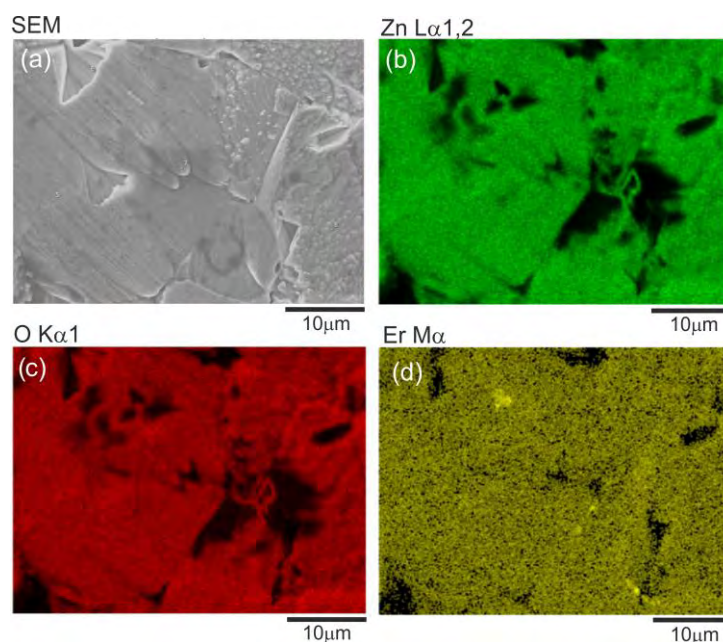


**Figure 4(a,b).** SEM images of the polished surface of 0.4%  $\text{Er}^{3+}$ -doped ZnO ceramic. The scale bar is (a)  $10 \mu\text{m}$  and (b)  $2 \mu\text{m}$ .

Figure 3 shows unpolarized Raman spectra of ZnO optical ceramics, undoped and doped with 0.4 wt% Er. All characteristic wurtzite vibrations are observed in the Raman spectra of both ZnO ceramics at 97, 202, 331, 378, 406, 438, 536, 663, 1096 and  $1153 \text{ cm}^{-1}$  [4]. A rise in the Raman spectrum of  $\text{Er}^{3+}$ -doped ceramics in the region of  $200\text{--}600 \text{ cm}^{-1}$  is explained by the contribution of Raman modes of  $\text{Er}_2\text{O}_3$ . The most intense Raman mode of  $\text{Er}_2\text{O}_3$  appears at  $\sim 380 \text{ cm}^{-1}$  [5] and overlaps with one of the modes characteristic for ZnO. As a result, the peak at  $\sim 378 \text{ cm}^{-1}$  is enhanced in the spectrum of  $\text{Er}^{3+}$ -doped ceramics.

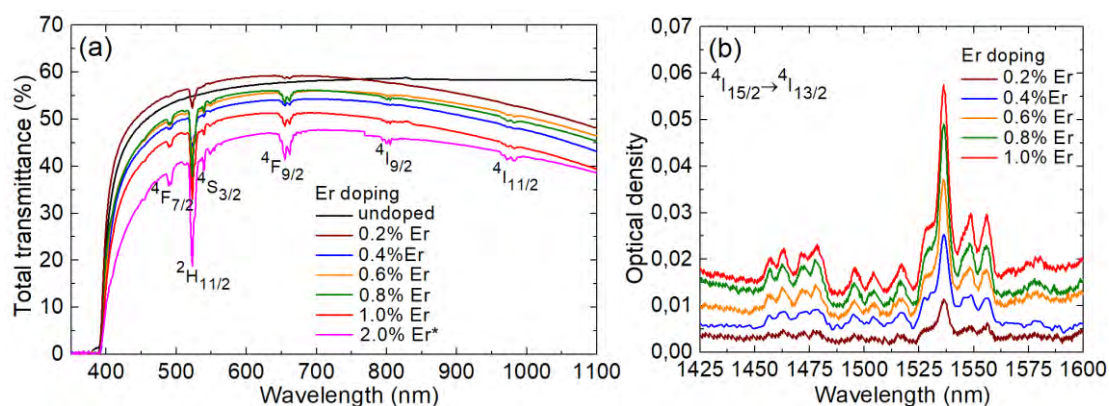
The analysis of the texture of the  $\text{Er}^{3+}$ -doped ZnO ceramics indicates that the main components of the texture are the (100) and (110) planes of the hexagonal prism, similar to those for the undoped ceramics. Erbium doping enhances the texture due to the preferred orientation of the prism planes. In the presence of erbium, conditions are created for orientation of the planes of the hexagonal pyramids with gently sloping faces (101), as compared to undoped ceramics.

Data on the nature of the texture of  $\text{Er}^{3+}:\text{ZnO}$  ceramics are consistent with the results of their study by SEM. Numerous grains with smooth facets of the prism and fine-bumpy facets of the negative monohedrons are visible on the surface of the polycrystalline sample, Figure 4(a). Facets of positive monohedrons with characteristic growth microhillocks in the form of hexagonal pyramids, Figure 4(b), are rare. Erbium addition into the ceramics leads to a decrease in the grain size: it ranges from 10 to 35  $\mu\text{m}$  for pure ZnO ceramic and from 5 to 15  $\mu\text{m}$  - for the  $\text{Er}^{3+}$ -doped ones.



**Figure 5(a-d).** EDX mapping of 0.4%  $\text{Er}^{3+}$ -doped ZnO ceramics: (a) SEM image, (b) zinc mapping (Zn  $L\alpha_{1,2}$ ), (c) oxygen mapping (O  $K\alpha_1$ ), and (d) erbium mapping (Er  $M\alpha$ ).

According to Figure 5, which shows the surface element mapping (Zn, O and Er) for the 0.4 wt%  $\text{Er}^{3+}$ -doped ZnO ceramics, regions with different microstructures have the same composition. They are formed by zinc, oxygen and erbium uniformly distributed over the sample. There are also irregularly distributed areas enriched in erbium and ranging in size from sub- $\mu\text{m}$  to a few  $\mu\text{m}$ . These are probably regions enriched in erbium oxide. These data illustrate the fact that  $\text{Er}^{3+}$  ions are located at ZnO grain boundaries and form the  $\text{Er}_2\text{O}_3$  crystals.

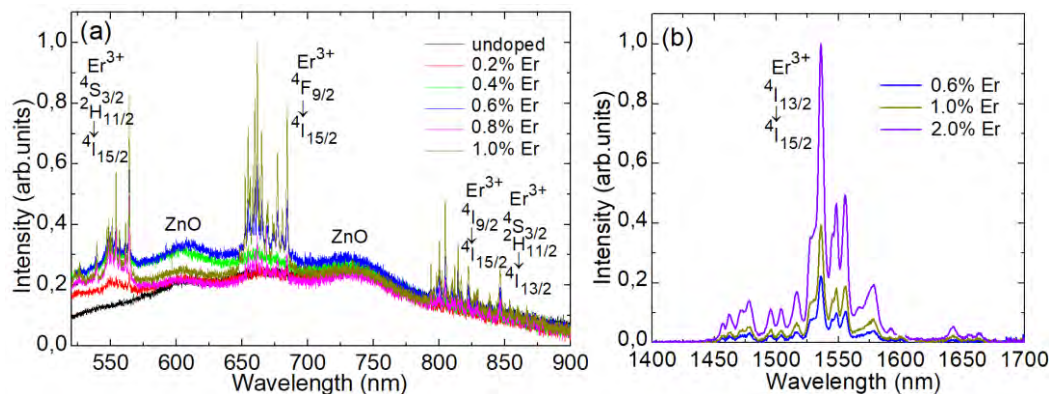


**Figure 6(a,b).** Optical absorption of  $\text{Er}^{3+}$ -doped ZnO ceramics: (a) total transmittance spectra. \*For the sample with 2.0% Er, the synthesis temperature is 1180  $^{\circ}\text{C}$ . (b) Absorption band related to the  ${}^4I_{15/2} \rightarrow {}^4I_{13/2}$   $\text{Er}^{3+}$  transition; the background scattering losses are subtracted and the spectra are shifted along the vertical axis for their comparison. The sample thickness is  $\sim 0.5$  mm.

Figure 6(a) shows the transmission spectra of undoped and Er<sup>3+</sup>-doped ZnO ceramics in the visible and near IR. All doped samples are characterized by a maximum in the transmission curves in the wavelength range 600 - 800 nm. The maximum transmission in the visible varies from ~60% to 45% with the Er content variation from 0.2 wt% up to 2.0 wt%. The UV absorption edge for Er<sup>3+</sup>-doped samples is about 390 nm. According to the study of transmission spectra in the mid-IR, the limit of the long-wavelength transparency of Er<sup>3+</sup>:ZnO ceramics shifts from ~4  $\mu\text{m}$  to 2.4-2.5  $\mu\text{m}$  as compared with the spectrum of undoped ceramic. This is a consequence of absorption by free carriers. Their concentration increases from  $3.13 \times 10^{18} \text{ cm}^{-3}$  (for undoped ZnO) to  $8.37 \times 10^{18} \text{ cm}^{-3}$  (for Er<sup>3+</sup>:ZnO).

In the spectra, bands characteristic of Er<sup>3+</sup> ions are observed at ~489, 522, 538, 654, 802 and 976 nm. They correspond to transitions in absorption from the <sup>4</sup>I<sub>15/2</sub> Er<sup>3+</sup> ground state to the excited states <sup>4</sup>F<sub>7/2</sub>, <sup>2</sup>H<sub>11/2</sub>, <sup>4</sup>S<sub>11/2</sub>, <sup>4</sup>F<sub>9/2</sub>, <sup>4</sup>I<sub>9/2</sub> and <sup>4</sup>I<sub>11/2</sub>, respectively. The Er<sup>3+</sup> absorption spectrum in the region of ~1.5  $\mu\text{m}$  (the <sup>4</sup>I<sub>15/2</sub> → <sup>4</sup>I<sub>13/2</sub> transition) has a fine structure, Figure 6(b). The shape of Er<sup>3+</sup> absorption bands for the Er<sup>3+</sup>:ZnO ceramics well agree with that for the Er<sub>2</sub>O<sub>3</sub> oxide [6]. The almost linear dependence of the optical density on the concentration of Er<sup>3+</sup> ions, Figure 6(b), indicates the implementation of Beer's law, i.e., the distribution of Er<sup>3+</sup> ions between the crystal interfaces and Er<sub>2</sub>O<sub>3</sub> crystals has a constant ratio. The Beer's law is verified for all absorption bands of Er<sup>3+</sup> ions.

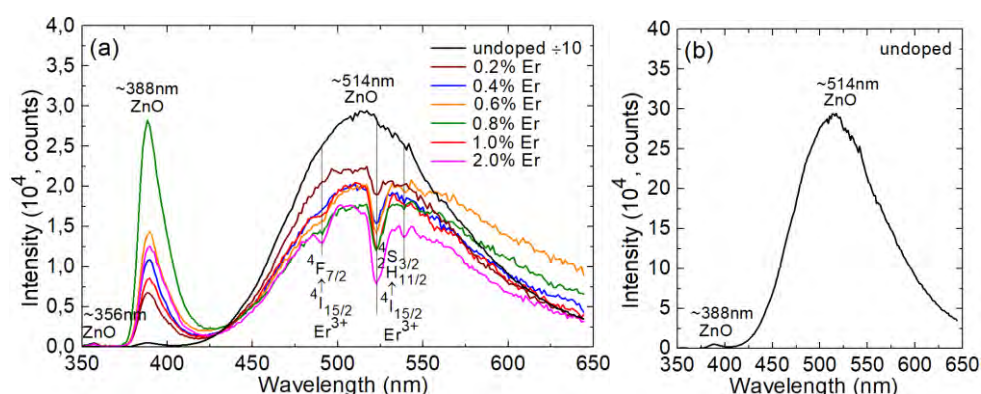
In the photoluminescence spectra upon excitation in the blue, Figure 7(a), structured bands assigned to the intra-4f shell Er<sup>3+</sup> emissions are observed. Besides that, broad underlying emission at ~500-900 nm with several local maxima at 600, 660 and 770 nm is clearly visible. It is assigned to transitions between various defect states in ZnO, as verified by the study of the undoped ceramics. In contrast, the fingerprint Er<sup>3+</sup> emission at ~1.5  $\mu\text{m}$ , Figure 7(b), has no underlying background. The intensity of the ~1.5  $\mu\text{m}$  luminescence gradually increases with the erbium content.



**Figure 7(a,b).** The spectra of photoluminescence of Er<sup>3+</sup>-doped ZnO ceramics: **(a)** visible spectral range,  $\lambda_{\text{exc}} = 488 \text{ nm}$ , **(b)** near-IR spectral range,  $\lambda_{\text{exc}} = 800 \text{ nm}$ . In **(a)**, the spectrum for undoped ceramics is given for comparison. For the sample with 2.0% Er, the synthesis temperature is 1180 °C.

X-ray luminescence spectroscopy is a powerful technique to observe the intrinsic and defect-related emissions of ZnO. The measured X-ray luminescence spectra, Figure 8, exhibit two intense emission bands. The first one is centered at ~389 nm and it is due to the near-band-edge (NBE) transitions. The second much broader band is centered at ~514 nm representing the defect state emission. The NBE emission intensity increases with the Er<sup>3+</sup> content exceeding 0.2 wt%. A significant suppression of the defect band is observed upon adding Er<sup>3+</sup> into the ceramics.

The average X-ray luminescence decay time in the “fast” time domain of 0–50 ns was 6–8 ns for all the studied Er<sup>3+</sup>-doped samples and about 65 ns for the undoped ZnO. In the “slow” domain of 50–200 ns, the decay time was 30–40 ns for Er<sup>3+</sup>-doped samples and 90 ns for the undoped ZnO ceramic.



**Figure 8(a,b).** The spectra of X-ray luminescence of (a)  $\text{Er}^{3+}$ -doped ZnO ceramics and (b) undoped ZnO ceramics. In (a), the spectrum for undoped ceramics is divided by a factor of 10. Vertical lines: absorption bands of  $\text{Er}^{3+}$  ions causing deeps in the X-ray luminescence spectra.

#### 4. Conclusions

Erbium ions do not enter the ZnO structure but are located on the ZnO grain surface and form the  $\text{Er}_2\text{O}_3$  phase at the grain boundaries. The planes of simple forms of  $\text{Er}^{3+}:\text{ZnO}$  grains have all morphological features typical for single crystals. The introduction of  $\text{Er}^{3+}$  ions enhances the texture inherent for undoped ceramics, but does not change its components. Er doping leads to a reduction of the ZnO grain size. In the Raman spectrum, vibrations characteristic of ZnO crystals are observed. A rise in the Raman spectrum of  $\text{Er}^{3+}$ -doped ceramics in the region of 200–600  $\text{cm}^{-1}$  is explained by the contribution of Raman modes of  $\text{Er}_2\text{O}_3$ .

The absorption spectra of  $\text{Er}^{3+}:\text{ZnO}$  ceramics contain the bands characteristic for  $\text{Er}_2\text{O}_3$ . The validity of the Beer's law is verified indicating the constant distribution of  $\text{Er}^{3+}$  ions between the surface of ZnO grains and the  $\text{Er}_2\text{O}_3$  phase. The  $\text{Er}^{3+}$  doping leads to a significant suppression of the intensity of the green (515–540 nm) ZnO X-ray luminescence band of defective nature, and to an enhancement of the exciton emission at 389 nm. It causes a change in the X-ray luminescence kinetics: the average decay time in the range of 0–50 ns for all Er-doped ceramics decreases by an order of magnitude compared to that for the undoped material. Photoluminescence spectra of ceramics upon excitation at 488 nm and 800 nm exhibit characteristic emission bands of the  $\text{Er}^{3+}$  ion. The spectral positions of the deeps in the X-ray luminescence spectra coincide with the absorption bands of  $\text{Er}^{3+}$  ions in  $\text{Er}_2\text{O}_3$ , indicating possible energy-transfer between the excitations to defect states in ZnO grains and  $\text{Er}^{3+}$  ions in  $\text{Er}_2\text{O}_3$ . The developed  $\text{Er}^{3+}$ -doped ZnO optical ceramics with transmittance of 40–60% in the visible spectral range possess a high radiation stability. They are promising for optoelectronic applications.

#### Acknowledgements

This work was partly supported by the RFBR (Grant 19-03-00855).

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